

AN11678

BGU8103UK GNSS LNA evaluation board

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Application note

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1. Introduction

NXP Semiconductors' BGU8103UK Global Navigation Satellite System (GNSS) LNA Evaluation Board is designed to evaluate the performance of the GNSS LNA using:

- NXP Semiconductors' BGU8103UK GNSS Low Noise Amplifier
- A matching inductor
- A decoupling capacitor

NXP Semiconductors' BGU8103UK is a low-noise amplifier for wearable receiver applications in an extremely small wafer level chip scale package WLCSP (SOT1445-1) at 0.69 mm x 0.44 mm x 0.29 mm. The BGU8103UK features gain of 18.5 dB and a noise figure of 0.80 dB at a current consumption of 1.2 mA. Its sufficient linearity performance removes interference and noise from co-habitation cellular transmitters, while retaining sensitivity. The LNA components occupy a total area of approximately 1.3 mm².

In this document, the application diagram, board layout, bill of materials, and typical results are given, as well as some explanations on GNSS related performance parameters like out-of-band input third-order intercept point O_{IIP3}, gain compression under jamming and noise under jamming.

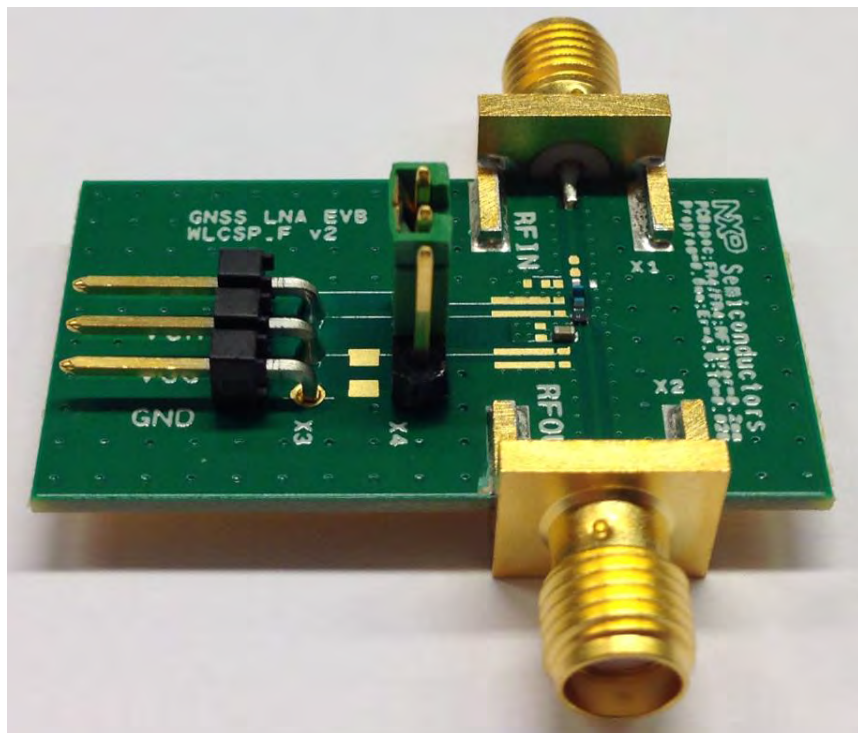


Fig 1. BGU8103UK GNSS LNA evaluation board

2. General description

Modern wearable applications like smartwatches suffer less from strong radio signals in the direct neighborhood, so problems like co-habitation are not likely to occur and linearity performance of a GNSS receiver may be reduced. To maximize battery life the power consumption of a GNSS receiver implemented in a wearable application should be as low as possible.

Since the GNSS receiver needs to receive signals with an average power level of -130 dBm, sensitivity is very important. Currently there are several GNSS chipsets on the market that can be implemented in wearable applications. Although many of these GNSS ICs do have integrated LNA front ends, the noise performance, and as a result the system sensitivity, is not always adequate. The GNSS receiver sensitivity is a measure how accurate the coordinates are calculated. The GNSS signal reception can be improved by a GNSS LNA, which improves the sensitivity by amplifying the wanted GNSS signal with a low-noise amplifier.

3. BGU8103UK GNSS LNA evaluation board

The BGU8103UK LNA evaluation board simplifies the RF evaluation of the BGU8103UK GNSS LNA applied in a GNSS front-end, often used in mobile cell phones. The evaluation board enables testing of the device RF performance and requires no additional support circuitry. The board is fully assembled with the BGU8103UK including the input series inductor and decoupling capacitor. The board is supplied with two SMA connectors for input and output connection to RF test equipment. The BGU8103UK can operate from a 1.5 V to 3.1 V single supply and consumes typical 1.2 mA.

3.1 Application Circuit

The circuit diagram of the evaluation board is shown in Fig 2. With jumper JU1 the enable input can be connected either to Vcc or GND.

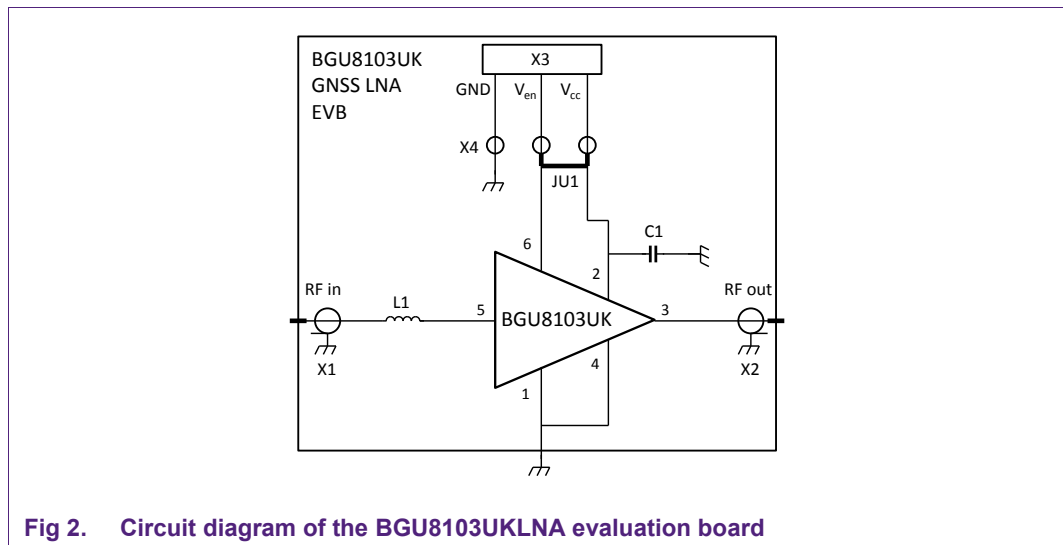


Fig 2. Circuit diagram of the BGU8103UK LNA evaluation board

3.2 PCB Layout

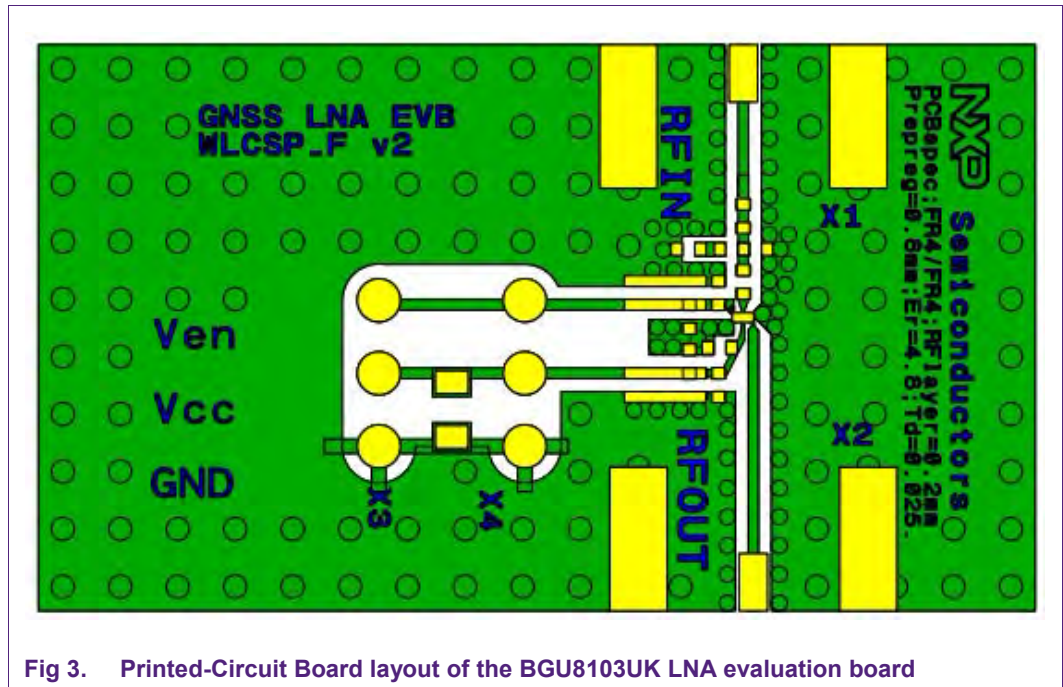
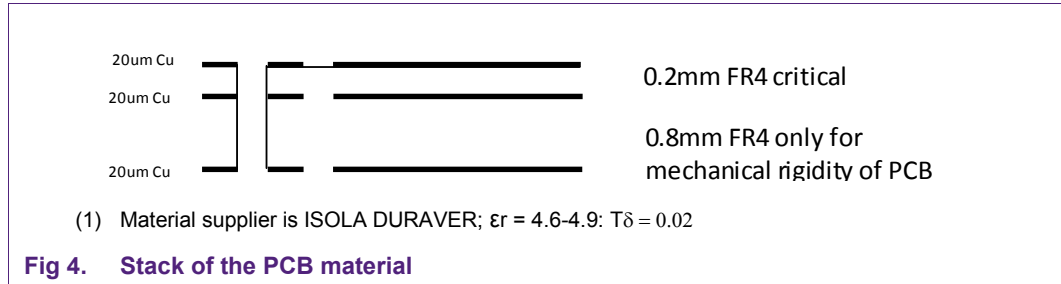


Fig 3. Printed-Circuit Board layout of the BGU8103UK LNA evaluation board

A good PCB layout is an essential part of an RF circuit design. The LNA evaluation board of the BGU8103UK can serve as a guideline for laying out a board using the BGU8103UK. Use controlled impedance lines for all high frequency inputs and outputs. Bypass Vcc with decoupling capacitors, preferably located as close as possible to the device. For long bias lines it may be necessary to add decoupling capacitors along the line further away from the device. Proper grounding of the GND pins is also essential for good RF performance. Either connect the GND pins directly to the ground plane or through vias, or do both, which is recommended. To ensure optimal performance of BGU8103UK in the application it is advised to simulate the overall application performance using the S-parameter and noise models of the device, the models for the external components (SAW filter, input inductor) and the models for the PCB. Models for the BGU8103UK are available via NXP sales representatives.

The material that has been used for the evaluation board is FR4 using the stack shown in Fig 4.



3.3 Bill of materials

Table 1. BOM of the BGU8103UK GNSS LNA evaluation board

Designator	Description	Footprint	Value	Supplier Name/type	Comment
-	BGU8103UK	0.69 mm x 0.44 mm x 0.29 mm		NXP	WLCSP
PCB		20 x 35mm		BGU8103UK GNSS LNA EV Kit	
C1	Capacitor	0402	1nF	Murata GRM1555	Decoupling
L1	Inductor	0402	12nH	Murata LQW15	Input matching
X1, X2	SMA RD connector	-	-	Johnson, End launch SMA 142-0701-841	RF input/ RF output
X3	DC header	-	-	Molex, PCB header, Right Angle, 1 row, 3 way 90121-0763	Bias connector
X4	JUMPER Stage	-	-	Molex, PCB header, Vertical, 1 row, 3 way 90120-0763	Connect Ven to Vcc or separate Ven voltage
JU1	JUMPER				

3.4 BGU8103UK product description

NXP Semiconductors’ BGU8103UK GNSS low noise amplifier is designed for the GNSS frequency band. The integrated biasing circuit is temperature stabilized, which keeps the current constant over temperature. It also enables the superior linearity performance of the BGU8103UK. The BGU8103UK is also equipped with an enable function that allows it to be controlled via a logic signal. In disabled mode it consumes less than 1 μ A.

The output of the BGU8103UK is internally matched for 1575.42 MHz whereas only one series inductor at the input is needed to achieve the best RF performance. Both the input and output are AC coupled via an integrated capacitor.

It requires only two external components to build a GNSS LNA having the following advantages:

- Low noise
- System optimized gain
- High linearity under jamming
- 0.69 mm x 0.44 mm x 0.29 mm: WLCSP (SOT1445-1)
- Low current consumption
- Short power settling time

3.5 Series inductor

The evaluation board is supplied with Murata LQW15 series inductor of 12 nH. This is a wire wound type of inductor with high quality factor (Q) and low series resistance (Rs) (see Table 2). This type of inductor is recommended in order to achieve the best noise performance. High Q inductors from other suppliers can be used. If it is decided to use other low cost inductors with lower Q and higher Rs the noise performance will degrade.

Table 2. Series Inductor options

Type	Murata	Size 0201	Size 0402	Size 0603	Comment
Multilayer Non-Magnetic Core	LQG		15H NF $\uparrow\uparrow$	18H NF \uparrow	
Film	LQP	03T NF $\uparrow\uparrow$	15M NF \uparrow		
Wirewound Non-Magnetic Core	LQW		15A Default	18A NF \downarrow	Lowest NF

4. Typical LNA evaluation board results

At the average power levels of -130 dBm that have to be received by a GNSS receiver, the system will not have in-band intermodulation problems caused by the GNSS-signal itself. Strong out-of-band cell phone TX jammers however can cause linearity problems, and result in third-order intermodulation products in the GNSS frequency band. In this chapter the effects of these Jammer-signals on the Noise and Gain performance of the BGU8103UK are described. The effect of these Jammers on the In-band and Out-of-Band

Third-Order Intercept points are described in more detail in a separate User Manual: UM10453: 2-Tone Test BGU7005 and BGU7007 GNSS LNA.

4.1 In-band 1dB gain compression due to 787MHz, 850MHz and 1850MHz jammers

As stated before, signal levels in the GNSS frequency band of -130 dBm average will not cause linearity problems in the GNSS band itself. This of course is also valid for the 1dB gain compression in-band. The 1dB compression point at 1575.42MHz caused by cell phone TX jammers however is important.

Measurements have been carried out using the setup shown in Fig 5.

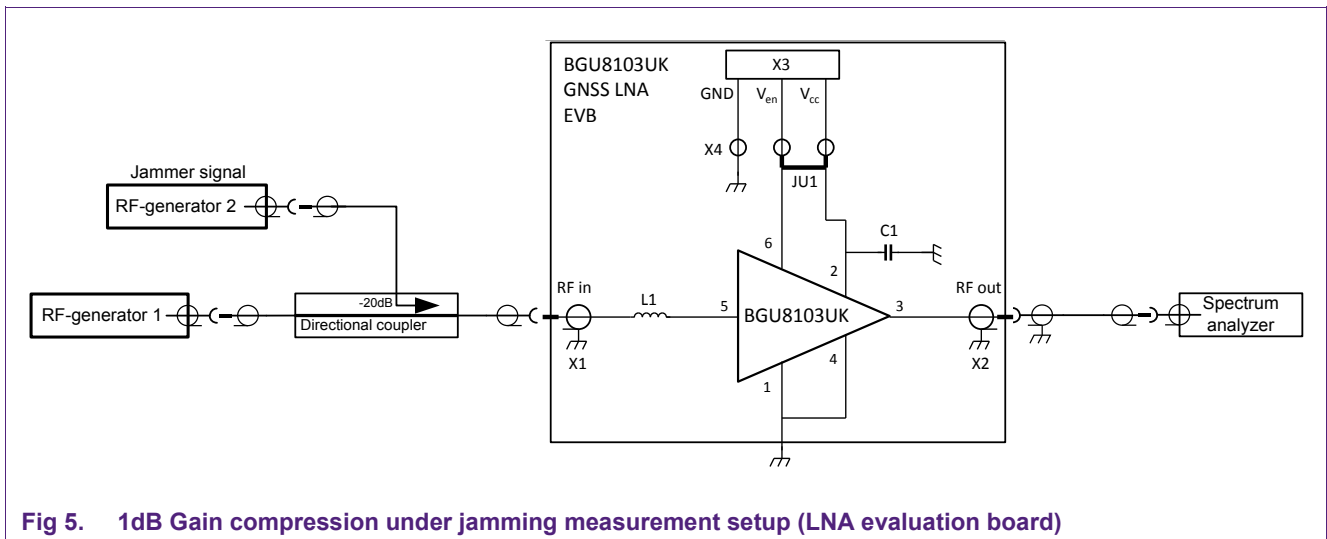
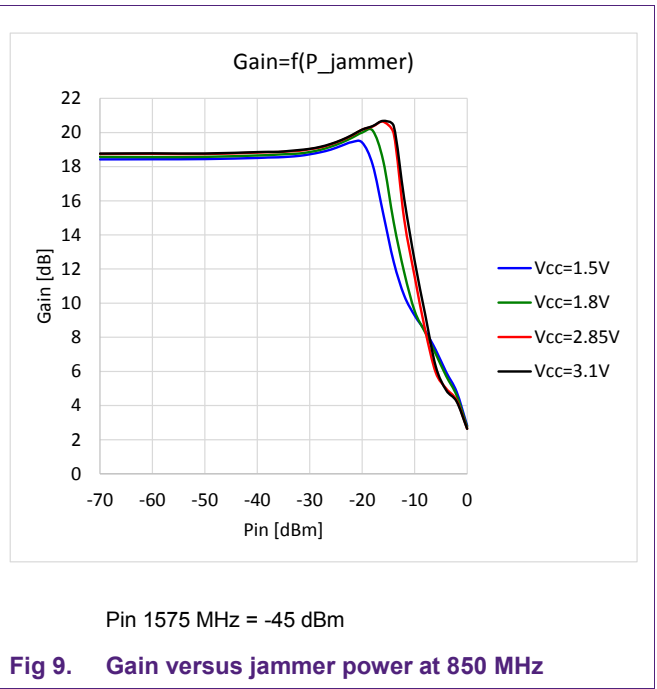
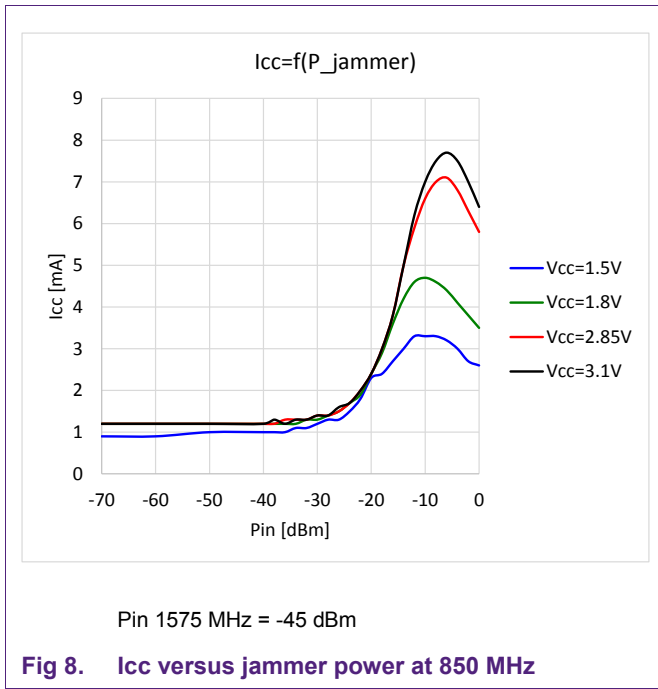
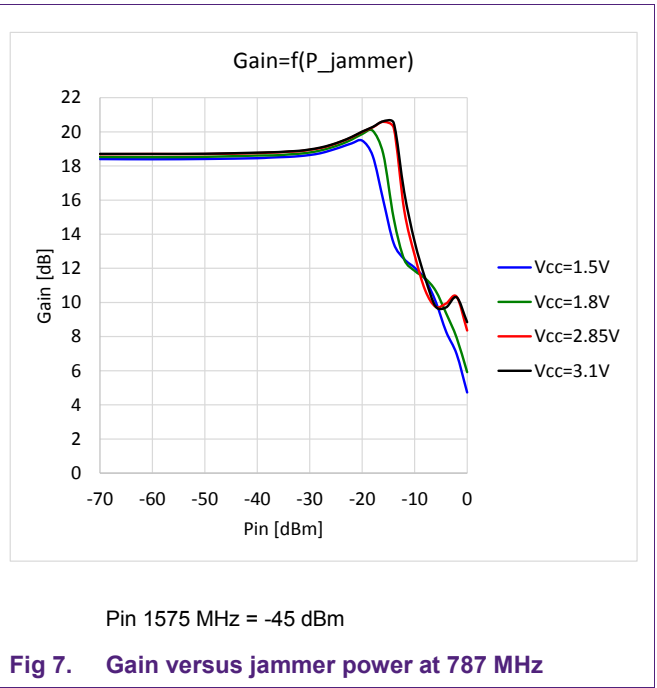
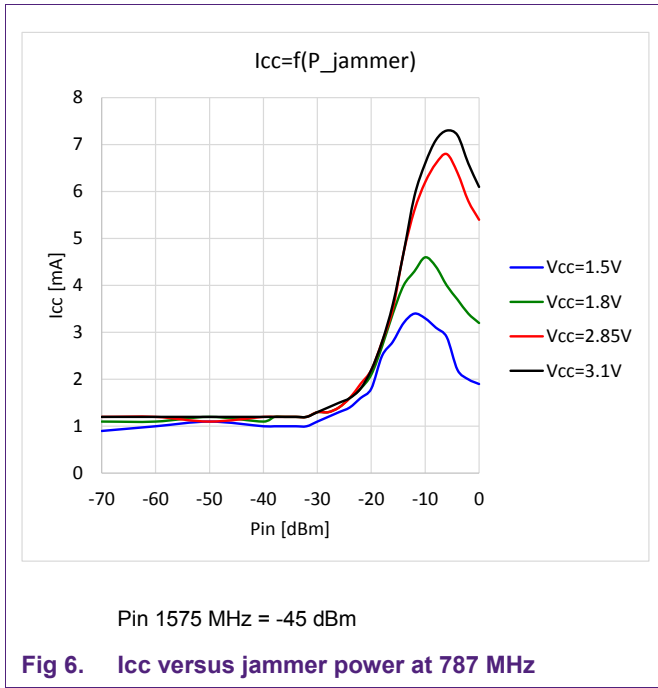


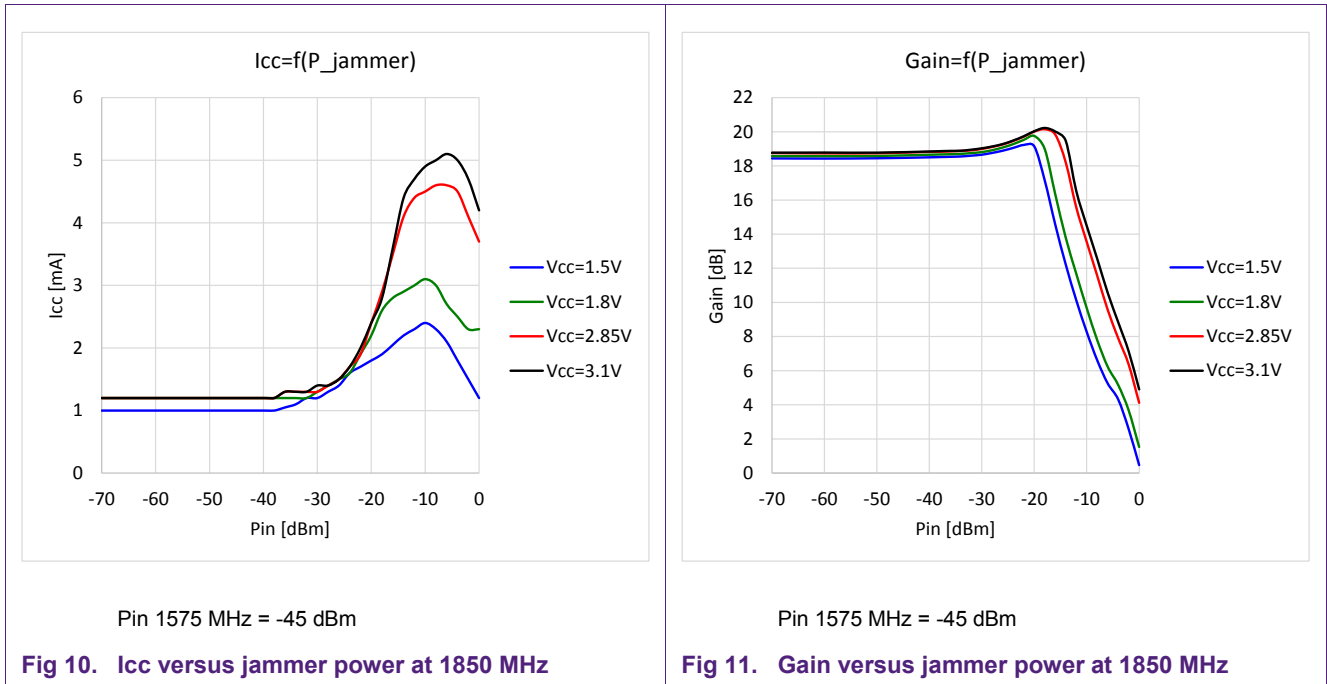
Fig 5. 1dB Gain compression under jamming measurement setup (LNA evaluation board)

The gain of the DUT was measured between port RFin and Rfout of the EVB at the GNSS frequency 1575 MHz, while simultaneously a jammer power signal was swept at the 20dB attenuated input port of the Directional Coupler. Please note that the drive power of the jammer is 20 dB lower at the input of the DUT caused by the directional coupler.

The figures below show the supply-current (I_{cc}) and gain compression curves with 787MHz, 850MHz and 1850 MHz jammers (input jammer power at LNA-board, taking into account the approx. 20 dB attenuation of the directional coupler and RF-cable from Jammer-Generator to the directional coupler).

The gain drops 1dB with approximately -12 dBm input jamming power at 787MHz and 850MHz ($V_{cc}=1.8V$) (Fig 7 and Fig 9). With an 1850MHz jamming signal, the 1dB gain compression occurs around -11 dBm input power level (Fig 11).

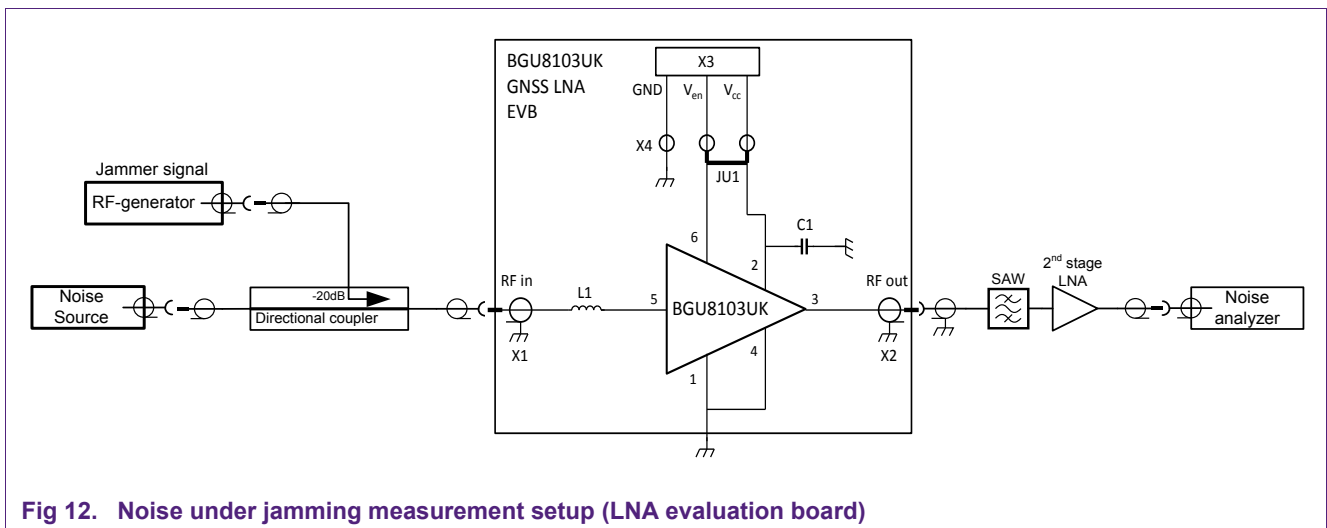




4.2 Noise figure as function of jammer power at 850MHz and 1850MHz

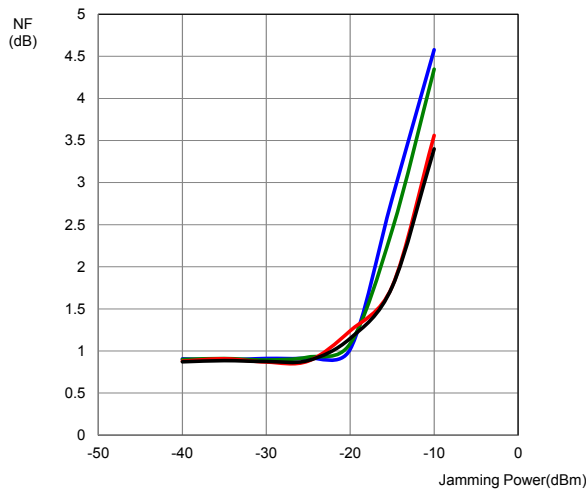
Noise figure under jamming conditions is a measure of how the LNA behaves when e.g. a GSM TX interfering signal is at the input of the GNSS antenna. To measure this behavior the setup shown in Fig 12 is used.

The jammer signal is coupled via a directional coupler to the DUT: this is to avoid the jammer signal damaging the noise source. The GNSS BPF is needed to avoid driving the second-stage LNA in saturation.



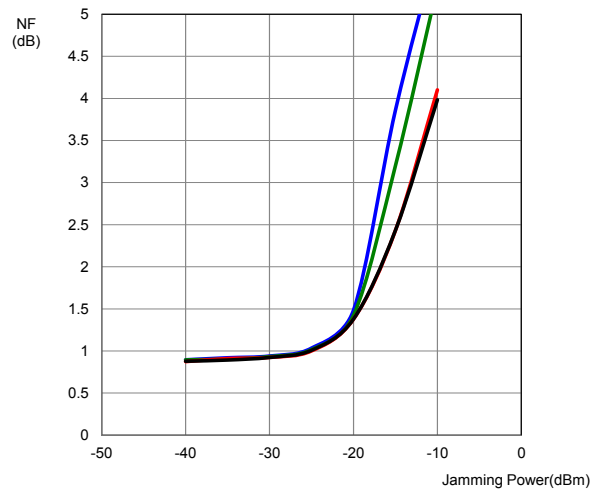
With the results of these measurements and the specification of the SAW filter, the jammer power levels that cause noise increase can be calculated.

As can be seen in Fig 13, with a 850 MHz jammer the NF of the LNA starts to increase at $P_{jam} = -20$ dBm (input jammer power at LNA-board, taking into account the approx. 20 dB attenuation of the directional coupler and RF-cable from Jammer-Generator to the directional coupler). For the 1850 MHz jammer the NF of the LNA starts to increase at $P_{jam} = -25$ dBm (see Fig 14).



fjam = 850 MHz; Tamb = 25 °C; f = 1575 MHz; including PCB losses.
 (1) Vcc = 1.5 V
 (2) Vcc = 1.8 V
 (3) Vcc = 2.85 V
 (4) Vcc = 3.1 V

Fig 13. NF versus jammer power at 850 MHz



fjam = 1850 MHz; Tamb = 25 °C; f = 1575 MHz; including PCB losses.
 (1) Vcc = 1.5 V
 (2) Vcc = 1.8 V
 (3) Vcc = 2.85 V
 (4) Vcc = 3.1 V

Fig 14. NF versus jammer power at 1850 MHz

5. Required Equipment

In order to measure the evaluation board the following is necessary:

- ✓ DC Power Supply up to 30 mA at 1.5 V to 3.1 V
- ✓ Two RF signal generators capable of generating RF signals at the operating frequency of 1575.42 MHz, as well as the jammer frequencies 1713.42 MHz and 1851.42 MHz
- ✓ An RF spectrum analyzer that covers at least the operating frequency of 1575.42 MHz as well as a few of the harmonics. Up to 6 GHz should be sufficient.
“Optional” a version with the capability of measuring noise figure is convenient
- ✓ Amp meter to measure the supply current (optional)
- ✓ A network analyzer for measuring gain, return loss and reverse isolation
- ✓ Noise figure analyzer and noise source
- ✓ Directional coupler
- ✓ Proper RF cables

6. Connections and setup

The BGU8103UK GNSS LNA evaluation board is fully assembled and tested. Please follow the steps below for a step-by-step guide to operate the LNA evaluation board and testing the device functions.

1. Connect the DC power supply to the V_{cc} and GND terminals. Set the power supply to the desired supply voltage, between 1.5 V and 3.1 V, but never exceed 3.1 V as it might damage the BGU8103UK.
2. Jumper JU1 is connected between the V_{cc} terminal of the evaluation board and the V_{en} pin of the BGU8103UK.
3. Connect the RF signal generator and the spectrum analyzer to the RF input and the RF output of the evaluation board, respectively. Do not turn on the RF output of the signal generator yet, set it to -45 dBm output power at 1575.42 MHz, set the spectrum analyzer at 1575.42 MHz center frequency and a reference level of 0 dBm.
4. Turn on the DC power supply and it should read approximately 1.2 mA.
5. Enable the RF output of the generator: The spectrum analyzer displays a tone around -26.5 dBm at 1575.42 MHz.
6. Instead of using a signal generator and spectrum analyzer one can also use a network analyzer in order to measure gain as well as in- and output return loss.
7. For noise figure evaluation, either a noise figure analyzer or a spectrum analyzer with noise option can be used. The use of a 5 dB noise source, like the Agilent 364B is recommended. When measuring the noise figure of the evaluation board, any kind of adaptors, cables etc between the noise source and the evaluation board should be minimized, since this affects the noise figure.

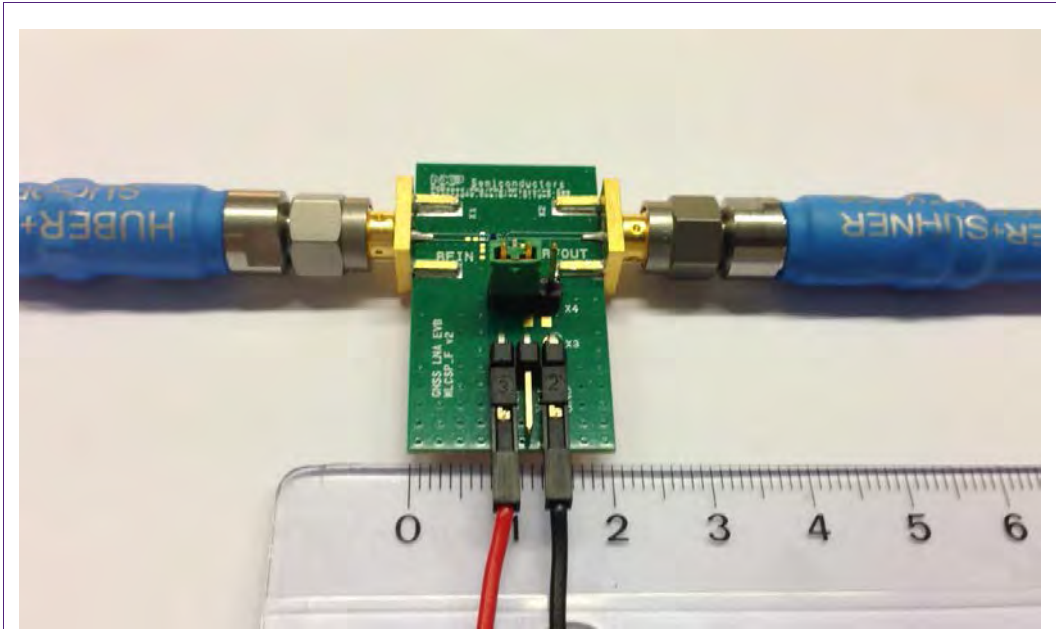


Fig 15. Evaluation board including its connections

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